

Power Modules for High Frequency Applications

Applications like battery chargers, welding, medical, or industrial power supplies operating at higher switching frequency in the range of several tens of kHz require power modules with optimized fast switching semiconductors and package layouts. Mitsubishi Electric is offering various products based on Si IGBT and SiC Technologies.



Technology Frequency Map









7th Gen. high speed TH-Series IGBT Modules

Turn-off loss (E_{off})

Features

- □ Latest 7th Gen. CSTBTTM IGBT and RFC-Diode technologies
- □ Half bridge Configuration
- Compatible pkg 48mm, 62mm and 80mm
- Low power loss at high switching frequency operation (fc: 20~60kHz)
- Optimized for trade-off of IGBT and Diode
- Low thermal resistance and high-power density by AIN ceramic substrate
- Low inductive package with 4kV insulation
- High temperature operation with T_{vjmax} = 175°C junction temperature at overload events



DC loss

The TH-Series IGBT is equipped with the latest 7th Generation CSTBTTM IGBT and RFC-Diode technology. The chip characteristics has been optimized for the needs of high frequency operation. For instance, comparing the 200A high speed TH-Series with 200A normal speed T-Series device, the turn-off switching energy (E_{off}) has been reduced by 56%. As result, a highly efficient operation at high frequency has been achieved.

Line-up TH-Series 2-in-1 High Speed IGBT Modules

Package	V _{CES} [V]	I _C [A]			
		200	400	600	
48 x 94 mm ²		CM200DY-24TH			
62 x 108 mm ²	1200V		CM400DY-24TH		
80 x 110 mm ²			CM400DU-24TH	CM600DU-24TH	
		-			





2nd Gen. Full SiC MOSFET Modules

Features

- Low inductance packages adopted to deliver full SiC performance
- Safe operation also in short circuit condition by RTC (Real Time current Control)
- □ Low power loss by 2nd Generation SiC
- **\Box** Wide range of switching frequency operation (f_c: 0~100 kHz)
- Low thermal resistance and high-power density by AIN ceramic substrate





Line-up 2nd Gen. Full SiC MOSFET Modules

Package	Model	V _{DSX} [V]	I _D [A]	Circuit	SC protection
121.7 x 92.3 mm ²	FMF600DXE-24BN	1200	600	0 1 4	
	FMF600DXE-34BN	1700		2-IN-1	-
121.7 x 92.3 mm ²	FMF400BX-24B		400	4-in-1	-
	FMF800DX-24B		800	2-in-1	sense source for external protection
62 x 108 mm ²	FMF400DY-24B	1200V	400	2-in-1	-
122 x 79.6 mm ²	FMF300BXZ-24B		300	4 10 4	RTC
	FMF400BXZ-24B		400	4-10-1	
A STAR	FMF600DXZ-24B		600		
	FMF800DXZ-24B		800	2-in-1	
	FMF300DXZ-34B	4700	300		
122 x 79.6 mm ²	FMF300E3XZ-34B	1700	300	Chopper	
122 x 152 mm ²	FMF1200DXZ-24B	1200	1200	2-in-1	





Industrial

Charging

Medical



NFH-Series High speed IGBT with optional SiC Diode

Features

- High Speed IGBT combined with SiC SB-Diode for recovery loss elimination
- Comprehensive Line-up 1200V , 100A ~ 600A half bridge configuration
- **\Box** Low power loss at high switching frequency operation (f_c: 20~60 kHz)
- Optimized for trade-off of IGBT and Diode
- Low thermal resistance and high power density by AIN ceramic substrate





Line-up 2-in-1 NFH-series High Speed Hybrid Modules

Package	V _{CES} [V]	I _C [A]					
		100	150	200	300	400	600
FERRE	1200	CMH100DY- 24NFH	CMH150DY- 24NFH				
A B B B				CMH200DU- 24NFH	CMH300DU- 24NFH		
JE BID						CMH400DU- 24NFH	CMH600DU- 24NFH

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Medical





Industrial

Charging